

Man Wong

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

206
papers

2,692
citations

29
h-index

44
g-index

240
ext. papers

3,057
ext. citations

2.7
avg, IF

5.07
L-index

#	Paper	IF	Citations
206	Nickel induced crystallization of amorphous silicon thin films. <i>Journal of Applied Physics</i> , 1998 , 84, 194-2005	2.9	213
205	High performance low temperature metal-induced unilaterally crystallized polycrystalline silicon thin film transistors for system-on-panel applications. <i>IEEE Transactions on Electron Devices</i> , 2000 , 47, 404-409	2.9	145
204	Characterization of the MIC/MILC interface and its effects on the performance of MILC thin-film transistors. <i>IEEE Transactions on Electron Devices</i> , 2000 , 47, 1061-1067	2.9	100
203	High-efficiency microcavity top-emitting organic light-emitting diodes using silver anode. <i>Applied Physics Letters</i> , 2006 , 88, 073517	3.4	87
202	Coupling efficiency enhancement in organic light-emitting devices using microlens array-theory and experiment. <i>Journal of Display Technology</i> , 2005 , 1, 278-282		84
201	Effects of longitudinal grain boundaries on the performance of MILC-TFTs. <i>IEEE Electron Device Letters</i> , 1999 , 20, 97-99	4.4	68
200	Comparative study of metal or oxide capped indium in oxide anodes for organic light-emitting diodes. <i>Journal of Applied Physics</i> , 2003 , 93, 3253-3258	2.5	61
199	Rapid thermal annealing of polysilicon thin films. <i>Journal of Microelectromechanical Systems</i> , 1998 , 7, 356-364	2.5	60
198	Identifying the Optimum Morphology in High-Performance Perovskite Solar Cells. <i>Advanced Energy Materials</i> , 2015 , 5, 1401775	21.8	57
197	Praseodymium oxide coated anode for organic light-emitting diode. <i>Applied Physics Letters</i> , 2002 , 80, 3485-3487	3.4	47
196	High-performance polycrystalline SiGe thin-film transistors using Al ₂ O ₃ gate insulators. <i>IEEE Electron Device Letters</i> , 1998 , 19, 502-504	4.4	43
195	Mechanism and Origin of Hysteresis in Oxide Thin-Film Transistor and Its Application on 3-D Nonvolatile Memory. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 438-446	2.9	41
194	Reversible Anion Exchange Reaction in Solid Halide Perovskites and Its Implication in Photovoltaics. <i>Journal of Physical Chemistry C</i> , 2015 , 119, 26883-26888	3.8	38
193	An Effective Channel Mobility-Based Analytical On-Current Model for Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 869-874	2.9	36
192	Self-Aligned Indium-Gallium-Zinc Oxide Thin-Film Transistor With Phosphorus-Doped Source/Drain Regions. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1150-1152	4.4	35
191	Efficient organic light-emitting diode using semitransparent silver as anode. <i>Applied Physics Letters</i> , 2005 , 87, 173505	3.4	35
190	The effects of high temperature annealing on metal-induced laterally crystallized polycrystalline silicon. <i>IEEE Transactions on Electron Devices</i> , 2000 , 47, 2061-2067	2.9	35

189	Self-Aligned Indium-Gallium-Zinc Oxide Thin-Film Transistor With Source/Drain Regions Doped by Implanted Arsenic. <i>IEEE Electron Device Letters</i> , 2013 , 34, 60-62	4.4	34
188	Degradation Behaviors of Metal-Induced Laterally Crystallized n-Type Polycrystalline Silicon Thin-Film Transistors Under DC Bias Stresses. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 225-232	2.9	34
187	Active-matrix organic light-emitting diode displays realized using metal-induced unilaterally crystallized polycrystalline silicon thin-film transistors. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 991-996	2.9	34
186	Zinc-Oxide Thin-Film Transistor With Self-Aligned Source/Drain Regions Doped With Implanted Boron for Enhanced Thermal Stability. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 393-399	2.9	33
185	Analytical solutions to the one-dimensional oxide-silicon-oxide system. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 1793-1800	2.9	33
184	. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 574-579	2.9	32
183	Characteristics of Thin-Film Transistors Fabricated on Fluorinated Zinc Oxide. <i>IEEE Electron Device Letters</i> , 2012 , 33, 549-551	4.4	32
182	Bridged-Grain Solid-Phase-Crystallized Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1414-1416	4.4	32
181	Top-emitting OLED using praseodymium oxide coated platinum as hole injectors. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1207-1210	2.9	31
180	Integrating Poly-Silicon and InGaZnO Thin-Film Transistors for CMOS Inverters. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3668-3671	2.9	30
179	Blue organic light-emitting diode based on 1,2,3,4,5-pentaphenyl-1-(8-phenyl-1,7-octadiynyl)silole. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2004 , 10, 10-15	3.8	30
178	Pressure loss in constriction microchannels. <i>Journal of Microelectromechanical Systems</i> , 2002 , 11, 236-244.5	4.5	30
177	Investigation of High-Performance ITO-Stabilized ZnO TFTs With Hybrid-Phase Microstructural Channels. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3174-3182	2.9	28
176	Performance of thin-film transistors with ultrathin Ni-MILC polycrystalline silicon channel layers. <i>IEEE Electron Device Letters</i> , 1999 , 20, 167-169	4.4	28
175	The Resistivity of Zinc Oxide Under Different Annealing Configurations and Its Impact on the Leakage Characteristics of Zinc Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1077-1084	2.9	26
174	Characterization of an individual grain boundary in metal-induced laterally crystallized polycrystalline silicon thin-film devices. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 1655-1660	2.9	26
173	Dopant and thickness dependence of metal-induced lateral crystallization of amorphous silicon films. <i>Journal of Applied Physics</i> , 2002 , 91, 1236-1241	2.5	26
172	Elevated-Metal-Metal-Oxide Thin-Film Transistor: Technology and Characteristics. <i>IEEE Electron Device Letters</i> , 2016 , 1-1	4.4	25

171	Analysis of Degradation Mechanisms in Low-Temperature Polycrystalline Silicon Thin-Film Transistors under Dynamic Drain Stress. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 1730-1737	2.9	24
170	. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 3276-3284	2.9	24
169	DC sputtered indium-tin oxide transparent cathode for organic light-emitting diode. <i>IEEE Electron Device Letters</i> , 2003 , 24, 315-317	4.4	23
168	High-performance staggered top-gate thin-film transistors with hybrid-phase microstructural ITO-stabilized ZnO channels. <i>Applied Physics Letters</i> , 2016 , 109, 182105	3.4	23
167	A Comparative Study on Fluorination and Oxidation of Indium-Gallium-Zinc Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2018 , 39, 196-199	4.4	22
166	. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 587-594	2.9	22
165	Polysilicon Thin Film-Transistors With Uniform and Reliable Performance Using Solution-Based Metal-Induced Crystallization. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 1244-1248	2.9	22
164	2016 ,		22
163	Characteristics of Plasma-Fluorinated Zinc Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1147-1149	4.4	21
162	A Quasi Two-Dimensional Conduction Model for Polycrystalline Silicon Thin-Film Transistor Based on Discrete Grains. <i>IEEE Transactions on Electron Devices</i> , 2008 , 55, 2148-2156	2.9	21
161	Dopant emission mechanism and the effects of host materials on the behavior of doped organic light-emitting diodes. <i>IEEE Transactions on Electron Devices</i> , 2002 , 49, 1540-1544	2.9	21
160	Fluorination-Enabled Monolithic Integration of Enhancement- and Depletion-Mode Indium-Gallium-Zinc Oxide TFTs. <i>IEEE Electron Device Letters</i> , 2018 , 39, 692-695	4.4	19
159	A Comparative Study on the Effects of Annealing on the Characteristics of Zinc Oxide Thin-Film Transistors With Gate-Stacks of Different Gas-Permeability. <i>IEEE Electron Device Letters</i> , 2014 , 35, 841-843	4.4	19
158	Analytical I-V relationship incorporating field-dependent mobility for a symmetrical DG MOSFET with an undoped body. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 1389-1397	2.9	19
157	An oxidation-last annealing for enhancing the reliability of indium-gallium-zinc oxide thin-film transistors. <i>Applied Physics Letters</i> , 2017 , 110, 142102	3.4	18
156	Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 1965-1970	2.9	18
155	Polycrystalline silicon films and thin-film transistors using solution-based metal-induced crystallization. <i>Journal of Display Technology</i> , 2006 , 2, 265-273		17
154	Characteristics of Elevated-Metal Metal-Oxide Thin-Film Transistors Based on Indium-Tin-Zinc Oxide. <i>IEEE Electron Device Letters</i> , 2017 , 38, 894-897	4.4	15

153	Two-Stage Degradation of p-Channel Poly-Si Thin-Film Transistors Under Dynamic Negative Bias Temperature Stress. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3034-3041	2.9	15
152	A comprehensive analytical on-current model for polycrystalline silicon thin film transistors based on effective channel mobility. <i>Journal of Applied Physics</i> , 2008 , 103, 094513	2.5	14
151	On the threshold Voltage of symmetrical DG MOS capacitor with intrinsic silicon body. <i>IEEE Transactions on Electron Devices</i> , 2004 , 51, 1600-1604	2.9	14
150	Anisotropic conduction behavior in metal-induced laterally crystallized polycrystalline silicon thin films. <i>Applied Physics Letters</i> , 2000 , 76, 448-450	3.4	14
149	Effects of substrate doping on the linearly extrapolated threshold voltage of symmetrical DG MOS devices. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 1616-1621	2.9	13
148	Synthesis, characterization and fabrication of ultrathin iron pyrite (FeS ₂) thin films and field-effect transistors. <i>RSC Advances</i> , 2016 , 6, 8290-8296	3.7	12
147	Characterization of DC-Stress-Induced Degradation in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 3206-3212	2.9	12
146	Thermally Induced Variation of the Turn-ON Voltage of an Indium-Gallium-Zinc Oxide Thin-Film Transistor. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 3703-3708	2.9	12
145	Fabrication of High-Performance Bridged-Grain Polycrystalline Silicon TFTs by Laser Interference Lithography. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 1085-1090	2.9	11
144	Geometric Effect Elimination and Reliable Trap State Density Extraction in Charge Pumping of Polysilicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2009 , 30, 517-519	4.4	11
143	An Analytical Expression for the Transfer Characteristics of a Polycrystalline Silicon Thin-Film Transistor With an Undoped Channel. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 1493-1498	2.9	11
142	Integrated micro-heat-pipe fabrication technology. <i>Journal of Microelectromechanical Systems</i> , 2003 , 12, 138-146	2.5	11
141	A Bottom-Gate Metal Oxide Thin-Film Transistor With Self-Aligned Source/Drain Regions. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2820-2826	2.9	11
140	Resilience of Fluorinated Indium-Gallium-Zinc Oxide Thin-Film Transistor Against Hydrogen-Induced Degradation. <i>IEEE Electron Device Letters</i> , 2020 , 41, 729-732	4.4	10
139	P-15: The Use of Fluorination to Enhance the Performance and the Reliability of Elevated-Metal Metal-Oxide Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 1235-1238	0.5	10
138	Study of the Characteristics of Solid Phase Crystallized Bridged-Grain Poly-Si TFTs. <i>IEEE Transactions on Electron Devices</i> , 2014 , 61, 1410-1416	2.9	10
137	Effects of high temperature post-annealing on the properties of solution-based metal-induced crystallized polycrystalline silicon films. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 355-358	2.1	10
136	Characterization of low-temperature processed single-crystalline silicon thin-film transistor on glass. <i>IEEE Electron Device Letters</i> , 2003 , 24, 574-576	4.4	10

135	High Precision Active-Matrix Self-Capacitive Touch Panel Based on Fluorinated ZnO Thin-Film Transistor. <i>Journal of Display Technology</i> , 2015 , 11, 22-29		9
134	A Physical Model for MetalOxide Thin-Film Transistor Under Gate-Bias and Illumination Stress. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 142-149	2.9	9
133	Threshold Voltage Adjustment in Hybrid-Microstructural ITO-Stabilized ZnO TFTs via Gate Electrode Engineering. <i>IEEE Electron Device Letters</i> , 2018 , 39, 975-978	4.4	9
132	Metal-replaced junction for reducing the junction parasitic resistance of a TFT. <i>IEEE Electron Device Letters</i> , 2006 , 27, 269-271	4.4	9
131	Floating low-temperature radio-frequency plasma oxidation of polycrystalline silicon-germanium. <i>Applied Physics Letters</i> , 1998 , 73, 360-362	3.4	9
130	Low-Power Design for Unipolar ITO-Stabilized ZnO TFT RFID Code Generator Using Differential Logic Decoder. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4768-4773	2.9	9
129	Suppression of the Short-Channel Effect in Dehydrogenated Elevated-Metal Metal- Oxide (EMMO) Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3001-3004	2.9	8
128	Suppressed Degradation of Elevated-Metal MetalOxide Thin-Film Transistors Under Bipolar Gate Pulse Stress. <i>IEEE Electron Device Letters</i> , 2018 , 39, 707-710	4.4	8
127	High-performance polycrystalline silicon thin-film transistors integrating sputtered aluminum-oxide gate dielectric with bridged-grain active channel. <i>Semiconductor Science and Technology</i> , 2013 , 28, 115003 ^{1,8}		8
126	24.3: Active-Matrix Organic Light-Emitting Diode Display Implemented Using Metal-Induced Unilaterally Crystallized Polycrystalline Silicon Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2001 , 32, 380	0.5	8
125	Implementation of linear doping profiles for high voltage thin-film SOI devices		8
124	Compact Modeling of Thin-Film Transistors for Flexible Hybrid IoT Design. <i>IEEE Design and Test</i> , 2019 , 36, 6-14	1.4	8
123	Significant Reduction of Dynamic Negative Bias Stress-Induced Degradation in Bridged-Grain Poly-Si TFTs. <i>IEEE Electron Device Letters</i> , 2015 , 36, 141-143	4.4	7
122	An Analytical Model for the Transfer Characteristics of a Polycrystalline Silicon Thin-Film Transistor With a Double Exponential Grain-Boundary Trap-State Energy Dispersion. <i>IEEE Electron Device Letters</i> , 2009 , 30, 1072-1074	4.4	7
121	A New Observation of the Elliot Curve Waveform in Charge Pumping of Poly-Si TFTs. <i>IEEE Electron Device Letters</i> , 2011 , 32, 506-508	4.4	7
120	Low-temperature annealing of polycrystalline Si/sub 1-x/Ge/sub x/ after dopant implantation. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 1958-1964	2.9	7
119	Three-mask polycrystalline silicon TFT with metallic gate and junctions. <i>IEEE Electron Device Letters</i> , 2006 , 27, 564-566	4.4	7
118	Self-Aligned Elevated-Metal Metal-Oxide Thin-Film Transistors for Displays and Flexible Electronics 2019 ,		7

117	OFF-State-Stress-Induced Instability in Switching Polycrystalline Silicon Thin-Film Transistors and Its Improvement by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1684-1687	4.4	7
116	Driving Stress-Induced Degradation in Polycrystalline Silicon Thin-Film Transistors and Its Suppression by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2017 , 38, 52-55	4.4	6
115	Degradation Induced by Forward Synchronized Stress in Poly-Si TFTs and Its Reduction by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1467-1470	4.4	6
114	A Novel Envelope Detector Based on Unipolar Metal-Oxide TFTs. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2020 , 67, 2367-2371	3.5	6
113	High stability fluorinated zinc oxide thin film transistor and its application on high precision active-matrix touch panel 2013 ,		6
112	A Two-Stage Degradation Model of p-Channel Low-Temperature Poly-Si Thin-Film Transistors Under Positive Bias Temperature Stress. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 3501-3505	2.9	6
111	An Analytical Expression for Threshold Voltage of Polycrystalline-Silicon Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2010 , 31, 815-817	4.4	6
110	Low Leakage Current Vertical Thin-Film Transistors With InSnO-Stabilized ZnO Channel. <i>IEEE Electron Device Letters</i> , 2020 , 41, 248-251	4.4	6
109	Enhanced Thermal Stability of Elevated-Metal Metal-Oxide Thin-Film Transistors via Low-Temperature Nitrogen Post-Annealing. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1649-1653	2.9	6
108	MEMS pressure sensors for high-temperature high-pressure downhole applications 2016 ,		6
107	The Implementation of Fundamental Digital Circuits With ITO-Stabilized ZnO TFTs for Transparent Electronics. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 5395-5399	2.9	6
106	Dynamic-Gate-Stress-Induced Degradation in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 3964-3970	2.9	5
105	Low-Temperature-Processed Power Schottky Diode Based on Amorphous Indium-Tin-Zinc-Oxide/Indium-Gallium-Zinc-Oxide Bilayer. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4759-4763	2.9	5
104	Series Resistance Extraction in Poly-Si TFTs With Channel Length and Mobility Variations. <i>IEEE Electron Device Letters</i> , 2011 , 32, 901-903	4.4	5
103	On the formation of solid state crystallized intrinsic polycrystalline germanium thin films. <i>Journal of Materials Research</i> , 1997 , 12, 2548-2551	2.5	5
102	Effects of high-temperature rapid thermal annealing on the residual stress of LPCVD-polysilicon thin films		5
101	35.4: A 2.1-inch AMOLED Display Based on Metal-Induced Laterally Crystallized Polycrystalline Silicon Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2004 , 35, 1128	0.5	5
100	P-128: Inverted Top-Emitting Organic Light-Emitting Devices Using Vanadium Pentoxide as Anode Buffer Layer. <i>Digest of Technical Papers SID International Symposium</i> , 2005 , 36, 793	0.5	5

99	Extracting the Critical Breakdown Electrical Field of Amorphous Indium-Gallium-Zinc-Oxide From the Avalanche Breakdown of n-Indium-Gallium-Zinc-Oxide/p+-Nickel-Oxide Heterojunction Diode. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1017-1020	4.4	4
98	Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor With Self-Aligned Definition of the Active Island. <i>IEEE Electron Device Letters</i> , 2018 , 39, 35-38	4.4	4
97	76.4: A Simple Technology for Realizing Self-Aligned Zinc Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2010 , 41, 1139	0.5	4
96	Effective Channel Mobility of Poly-Silicon Thin Film Transistors 2006 ,		4
95	High-Performance Polycrystalline Silicon Thin-Film Transistors without Source/Drain Doping by Utilizing Anisotropic Conductivity of Bridged-Grain Lines. <i>Advanced Electronic Materials</i> , 2020 , 6, 1900961	6.4	4
94	P-1.1: Characterization of the Off-State Current of an Elevated-Metal Metal-Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 413-416	0.5	4
93	Fluorinated indium-gallium-zinc oxide thin-film transistor with reduced vulnerability to hydrogen-induced degradation. <i>Journal of the Society for Information Display</i> , 2020 , 28, 520-527	2.1	3
92	Reversely-Synchronized-Stress-Induced Degradation in Polycrystalline Silicon Thin-Film Transistors and Its Suppression by a Bridged-Grain Structure. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1213-1216	4.4	3
91	Realization and Characterization of a Bulk-Type All-Silicon High Pressure Sensor. <i>Journal of Microelectromechanical Systems</i> , 2018 , 27, 231-238	2.5	3
90	Investigation of top gate GaN thin-film transistor fabricated by DC magnetron sputtering. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2018 , 36, 032203	1.3	3
89	A Self-Scanned Active-Matrix Tactile Sensor Realized Using Silicon-Migration Technology. <i>Journal of Microelectromechanical Systems</i> , 2015 , 24, 677-684	2.5	3
88	Instability of p-channel poly-Si thin-film transistors under dynamic negative bias temperature stress 2010 ,		3
87	Wide-band piezoresistive aero-acoustic microphone 2011 ,		3
86	Solution-based metal induced crystallized polycrystalline silicon films and thin-film transistors. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 117-121	2.1	3
85	27.4: Top-emitting Organic Light-Emitting Diode using Nanometer Platinum Layers as Hole Injector. <i>Digest of Technical Papers SID International Symposium</i> , 2003 , 34, 974	0.5	3
84	Reduction of threshold voltage in metal-induced-laterally-crystallized thin film transistors		3
83	Fluorinated Metal-Oxide Thin-Film Transistors for Circuit Implementation on a Flexible Substrate 2022 , 1-1		3
82	P-22: Turn-On Voltage Modulation of Indium-Gallium-Zinc-Oxide Thin-Film Transistors through Thermal Annealing Processes. <i>Digest of Technical Papers SID International Symposium</i> , 2016 , 47, 1197-1199	0.5	3

81	Neuromorphic Implementation of Logic Functions Based on Parallel Dual-Gate Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	3
80	P-11: Carrier Concentration Reduction by Fluorine Doping in P-Type SnO Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 1251-1254	0.5	2
79	Gate Insulator Engineering in Top-Gated Indium-Tin-Oxide-Stabilized ZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1104-1107	4.4	2
78	. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1338-1341	4.4	2
77	Degradation of Polycrystalline Silicon TFT CMOS Inverters under AC Operation. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 295-300	2.9	2
76	A 1200-atmosphere bulk-type all-silicon pressure sensor 2017 ,		2
75	A technology for monolithic MEMS-CMOS integration and its application to the realization of an active-matrix tactile sensor 2014 ,		2
74	Wide-band piezoresistive microphone for aero-acoustic applications 2012 ,		2
73	Metal-Induced Continuous Zonal Domain (CZD) Polycrystalline Silicon Thin-Film Transistors and Its Application on Field Sequential Color Liquid Crystal Display. <i>Journal of Display Technology</i> , 2010 , 6, 135-141		2
72	Negative drain pulse stress induced two-stage degradation of P-channel poly-Si thin-film transistors 2011 ,		2
71	A Reduced Mask-Count Technology for Complementary Polycrystalline Silicon Thin-Film Transistors With Self-Aligned Metal Electrodes. <i>IEEE Electron Device Letters</i> , 2009 , 30, 33-35	4.4	2
70	P-5: Self-Release Nickel Induced Lateral Crystallized (SR-NILC) Low Temperature Polycrystalline Silicon Films and Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2009 , 40, 1096	0.5	2
69	Degradation of solution based metal induced laterally crystallized p-type poly-Si TFTs under DC bias stresses 2008 ,		2
68	P-230: Novel Electrical-Chemically Polished Stainless Steel Anode Organic Light Emission Device with Long Lifetime at High Luminance for Flexible Lighting. <i>Digest of Technical Papers SID International Symposium</i> , 2008 , 39, 2064	0.5	2
67	Characteristics and stability of improved re-crystallized metal-induced laterally crystallized polycrystalline-silicon thin-film transistors for display applications. <i>Journal of the Society for Information Display</i> , 2003 , 11, 633	2.1	2
66	A micro-channel heat sink with integrated temperature sensors for phase transition study 1999 ,		2
65	A High Gain Low-Noise Amplifier Based on ITO-Stabilized ZnO Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 5537-5543	2.9	2
64	Reliability of Poly-Si TFTs under Voltage Pulse with Fast Transition Time. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	2

63	A Timing Model for the Optimal Design of a Prototype Active-Matrix Display. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3167-3174	2.9	2
62	Evaluation of Positive-Bias-Stress-Induced Degradation in InSnZnO Thin-Film Transistors by Low Frequency Noise Measurement. <i>IEEE Electron Device Letters</i> , 2022 , 1-1	4.4	2
61	A Planar Single-Actuator Bi-Stable Switch Based on Latch-Lock Mechanism 2019 ,		1
60	24-2: Distinguished Student Paper: Fluorination for Enhancing the Resistance of Indium-Gallium-Zinc Oxide Thin-Film Transistor against Hydrogen-Induced Degradation. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 347-350	0.5	1
59	Passivation of Poly-Si Thin Film Employing Si Self-Implantation and Its Application to TFTs. <i>IEEE Journal of the Electron Devices Society</i> , 2018 , 6, 240-244	2.3	1
58	P-130: Reliable Flexible Elevated Metal Metal-Oxide IGZO TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 1587-1589	0.5	1
57	59.3: Bridged-grain (BG) Eximer Laser Annealing (ELA) Polycrystalline Silicon Thin Film Transistors (TFTs). <i>Digest of Technical Papers SID International Symposium</i> , 2011 , 42, 870-873	0.5	1
56	The design, fabrication and characterization of a piezoresistive tactile sensor for fingerprint sensing 2010 ,		1
55	Positive bias temperature stress induced degradation in p-channel poly-Si thin-film transistors 2011 ,		1
54	Degradation of static behaviour of poly-Si CMOS inverters under high frequency operation 2011 ,		1
53	Optimization of charge pumping technique in polysilicon TFTs for geometric effect elimination and trap state density extraction 2008 ,		1
52	P-15: A 3 inch Active Matrix for Color Sequential- Liquid Crystal Display (CS-LCD) Based on Metal Induced Continuous Zonal Domain (CZD) Polycrystalline Silicon Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2008 , 39, 1223	0.5	1
51	Post-annealing of solution-based metal-induced laterally crystallized poly-Si with triple-frequency YAG laser. <i>Journal of Materials Science: Materials in Electronics</i> , 2007 , 18, 351-354	2.1	1
50	Super-Large Domain Metal-Induced Radially Crystallized Poly-Si Made Using Ni(NO ₃) ₂ /NH ₄ OH Mixed Solution. <i>Journal of Electronic Materials</i> , 2007 , 36, 1160-1165	1.9	1
49	P-17: Metal Induced Continuous Zonal Domain Polycrystalline Silicon and Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2007 , 38, 233-236	0.5	1
48	P-10 Post-Crystallization of Metal-Induced Laterally Crystallized Poly-Si with YAG Laser. <i>Digest of Technical Papers SID International Symposium</i> , 2006 , 37, 227	0.5	1
47	Experimental investigation of electrokinetically generated in-plane vorticity in a microchannel		1
46	Parallel and series multiple microchannel systems		1

45	Investigation of heavily doped silicon as an anode material for top-emitting organic light-emitting diode		1
44	Characteristics of transistors fabricated on silicon-on-quartz prepared using a mechanically initiated exfoliation technique. <i>IEEE Electron Device Letters</i> , 2005 , 26, 607-609	4.4	1
43	Suppression of leakage current in low-temperature metal-induced unilaterally crystallized polycrystalline silicon thin-film transistor using an improved process sequence and a gate-modulated lightly-doped drain structure		1
42	Application of metal-induced unilaterally crystallized polycrystalline silicon thin-film transistor technology to active-matrix organic light-emitting diode displays		1
41	Reverse short-channel effect in metal-induced laterally crystallized polysilicon thin-film transistors. <i>IEEE Electron Device Letters</i> , 1999 , 20, 566-568	4.4	1
40	P-4: Enhanced Scalability and Reliability of High Mobility Elevated-Metal Metal-Oxide Thin-Film Transistors with Bandgap Engineering. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 1322-1325	0.5	1
39	A Unified Degradation Model of Elevated-Metal Metal Oxide (EMMO) TFTs Under Positive Gate Bias With or Without an Illumination. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 1081-1087	2.9	1
38	P-11: Self-Heating Induced Degradation in a Metal-Oxide Thin-Film Transistor on a Flexible Substrate and Its Mitigation. <i>Digest of Technical Papers SID International Symposium</i> , 2021 , 52, 1092-1095 ^{0.5}		1
37	Thermal Budget Reduction in Metal Oxide Thin-Film Transistors via Planarization Process. <i>IEEE Electron Device Letters</i> , 2021 , 42, 180-183	4.4	1
36	P-1.5: Edge Effects of Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor and Their Elimination. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 531-534	0.5	1
35	8.1: Invited Paper: Enhanced Elevated-Metal Metal-Oxide Thin-Film Transistor Technology. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 75-78	0.5	1
34	Reliable High-Performance Amorphous InGaZnO Schottky Barrier Diodes With Silicon Dioxide Passivation Layer. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1338-1341	4.4	1
33	Stacked-Interconnect for Monolithic Integration of Low-Temperature Polysilicon and Amorphous Metal-Oxide Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1331-1333	4.4	1
32	Ultraviolet to Near-Infrared Broadband Phototransistors Based on Hybrid InGaZnO/C8-BTBT Heterojunction Structure. <i>IEEE Electron Device Letters</i> , 2021 , 1-1	4.4	1
31	Low-Frequency Noise in Bridged-Grain Polycrystalline Silicon Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 1984-1988	2.9	1
30	Self-Compensation Effect of Photo-Bias Instabilities in a-InGaZnO Thin-Film Transistors Induced by Unique Ion Migration. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-7	2.9	1
29	A Comparative Study on Inverters Built With Dual-Gate Thin-Film Transistors Based on Depletion- or Enhancement-Mode Technologies. <i>IEEE Transactions on Electron Devices</i> , 2022 , 1-6	2.9	1
28	P-1: Peripherally Crystallized Polycrystalline Silicon (PCP) for Thin-Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2005 , 36, 224	0.5	0

27	15.1: Invited Paper: A Low-Temperature Elevated-Metal Metal-Oxide Thin-Film Transistor Technology for Flexible Electronics. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 202-205</i>	0.5	0
26	Compact Integration of Hydrogen-Resistant $\alpha\text{-InGaZnO}$ and Poly-Si Thin-Film Transistors. <i>Micromachines, 2022, 13, 839</i>	3.3	0
25	P-15: Gate-Bias-Stress-Induced Instability in Hybrid-Phase Microstructural ITO-Stabilized ZnO TFTs. <i>Digest of Technical Papers SID International Symposium, 2019, 50, 1267-1270</i>	0.5	
24	1.3: A Timing Model for the Design of an Active-Matrix Display. <i>Digest of Technical Papers SID International Symposium, 2019, 50, 13-16</i>	0.5	
23	8.2: Invited Paper: Elevated-Metal Metal-Oxide Thin-Film Transistor with Self-Aligned Source/Drain Regions. <i>Digest of Technical Papers SID International Symposium, 2019, 50, 75-78</i>	0.5	
22	Schottky Barrier Controlled Conduction in Poly-Si TFTs With Metal Source and Drain. <i>IEEE Transactions on Electron Devices, 2013, 60, 1958-1964</i>	2.9	
21	Passivation Effects of Aluminum on Polycrystalline Silicon Thin-Film Transistor With Metal-Replaced Junctions. <i>IEEE Electron Device Letters, 2007, 28, 126-128</i>	4.4	
20	P-168: Investigation of High-Efficiency Electrophosphorescent Organic Light-emitting Diodes with Double-Emission Layers. <i>Digest of Technical Papers SID International Symposium, 2007, 38, 826-829</i>	0.5	
19	32.3: Metal-Induced Unilaterally Crystallized Polycrystalline Silicon Thin-Film Transistor Technology for Active-Matrix Organic Light-Emitting Diode Displays with Reduced Susceptibility to Cross-Talk. <i>Digest of Technical Papers SID International Symposium, 2002, 33, 976</i>	0.5	
18	47.2: Hole Injection and Power Efficiency of Organic Light Emitting Diodes with Ultra-Thin Inorganic Buffer Layer on Indium Tin Oxide. <i>Digest of Technical Papers SID International Symposium, 2002, 33, 1262</i>	0.5	
17	P-2: Re-Crystallized Metal-Induced Laterally Crystallized Polycrystalline Silicon for System-on-Panel Applications. <i>Digest of Technical Papers SID International Symposium, 2000, 31, 531-533</i>	0.5	
16	Low-Temperature Floating Plasma Oxidation of Poly-SiGe. <i>Materials Research Society Symposia Proceedings, 1998, 508, 157</i>		
15	Effect of Interface Modification Conditions on Electrical Characteristics and Device Consistency of Organic Thin Film Transistors. <i>IEEE Electron Device Letters, 2022, 43, 36-39</i>	4.4	
14	A cost-effective fluorination method for enhancing the performance of metal oxide thin-film transistors. <i>Journal of the Society for Information Display, 2021, 29, 318-327</i>	2.1	
13	P-19: Student Poster: Enhanced Elevated-Metal Metal-Oxide Thin-Film Transistors for Gate-Driver Circuit Fabricated on a Flexible Substrate. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 1124-1127</i>	0.5	
12	8-1: Distinguished Paper: A Cost-Effective Fluorination Method for Enhancing the Performance of Metal Oxide Thin-Film Transistors Using a Fluorinated Planarization Layer. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 77-80</i>	0.5	
11	P-18: Student Poster: Non-Oxidizing Pre-Annealing for Enhanced Fluorination of an Indium-Gallium-Zinc Oxide Thin-Film Transistor. <i>Digest of Technical Papers SID International Symposium, 2021, 52, 1120-1123</i>	0.5	
10	Dimension Scaling Effects on Conduction and Low Frequency Noise Characteristics of ITO-Stabilized ZnO Thin Film Transistors. <i>IEEE Journal of the Electron Devices Society, 2020, 8, 435-441</i>	2.3	

9	P-1.4: Elevated-Metal Metal-Oxide Thin-Film Transistor with Fluorinated Indium-Gallium-Zinc Oxide Channel towards Flexible Applications. <i>Digest of Technical Papers SID International Symposium, 2018</i> , 49, 528-530	0.5
8	24.3: Short-Channel Indium-Gallium-Zinc Oxide Thin-Film Transistor Enabled by Thermal Dehydrogenation and Oxidizing Defect-Suppression. <i>Digest of Technical Papers SID International Symposium, 2018</i> , 49, 255-258	0.5
7	30.1: Transparent Basic Logic Circuits with ITO-Stabilized ZnO Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium, 2018</i> , 49, 322-325	0.5
6	P-21: Three-Mask Elevated-Metal Metal-Oxide Thin-Film Transistor Technology for High-Resolution AMOLED Application. <i>Digest of Technical Papers SID International Symposium, 2018</i> , 49, 1256-1259	0.5
5	29.5: Reliability Enhancement of an Indium-Gallium-Zinc Oxide Thin-Film Transistor by Pre-Fluorination Non-Oxidizing Annealing. <i>Digest of Technical Papers SID International Symposium, 2021</i> , 52, 403-406	0.5
4	2.2: High-Resolution Active-Matrix Organic Light-Emitting Diode Display Realized Using Elevated-Metal Metal-Oxide Transistor Technology. <i>Digest of Technical Papers SID International Symposium, 2021</i> , 52, 51-51	0.5
3	P-1.2: All-Oxide Thin-Film Transistors for Low-Voltage-Operation Circuits. <i>Digest of Technical Papers SID International Symposium, 2021</i> , 52, 688-691	0.5
2	Effect of Moisture Exchange Caused by Low-Temperature Annealing on Device Characteristics and Instability in InSnZnO Thin-Film Transistors. <i>Advanced Materials Interfaces</i> , 2102584	4.6
1	Elevated-Metal Metal-Oxide Thin-Film Transistors: A Back-Gate Transistor Architecture with Annealing-Induced Source/Drain Regions 2022 , 273-313	